PTVSHC3N12VUT



Transient Voltage Suppressor

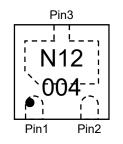
Description

The PTVSHC3N12VUT transient voltage suppressor is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's.

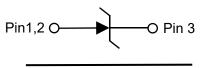
They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The PTVSHC3N12VUT protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events.

The PTVSHC3N12VUT is available in a DFN2020-3L package with working voltages of 12 volt.

It is used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (\pm 30kV air, \pm 30kV contact discharge)



Marking (Top View)



Circuit Diagram

Feature

- 6300W Peak pulse power per line (t_P = 8/20µs)
- DFN2020-3L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30kV(air), 30kV(contact);
 IEC 61000-4-5 (Lightning) 210A (8/20us)

Applications

- Power Management
- Industrial Application
- Power Supply Protection
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- > Peripherals

Mechanical Characteristics

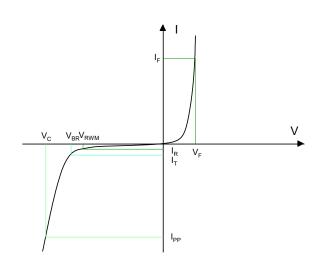
- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Pure tin plating: 7 ~ 17 um

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Electronics Parameter

Symbol	Parameter		
V _{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V _{RWM}		
V _{BR}	Breakdown Voltage @ I _T		
Ι _Τ	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
V _c	Clamping Voltage @ I _{PP}		
P _{PP}	Peak Pulse Power		
CJ	Junction Capacitance		
I _F	Forward Current		
V _F	Forward Voltage @ I _F		



Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}	-	-	-	12	V
Breakdown Voltage	V _{BR}	l _t = 1mA	13	14	16	V
Reverse Leakage Current	۱ _R	V _{RWM} = 12V	-	-	1.0	μA
Clamping Voltage	V _c	$I_{PP} = 210A, t_P = 8/20\mu s$	-	26	30	V
Junction Capacitance	CJ	$V_R = 0V, f = 1MHz$	-	-	1550	pF

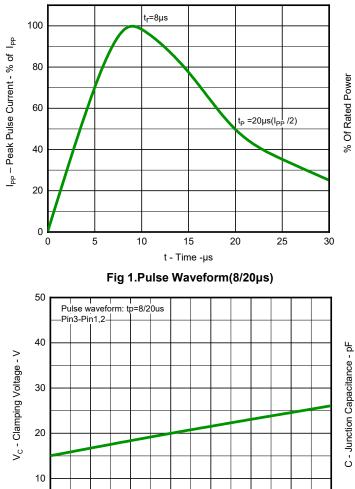
Absolute maximum rating@25°C

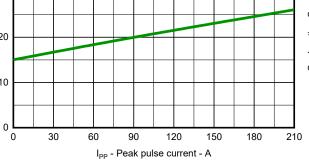
Rating	Symbol	Value	Units
Peak Pulse Power ($t_P = 8/20 \mu s$)	P _{PP}	6300	W
Peak Pulse Current (t _P = 8/20µs)	I _{PP}	210	А
Lead Soldering Temperature	TL	260 (10 sec)	°C
Junction and Storage Temperature Range	T _{J,} T _{STG}	-55~+150	°C

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Typical Characteristics







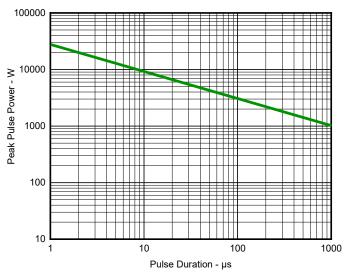


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

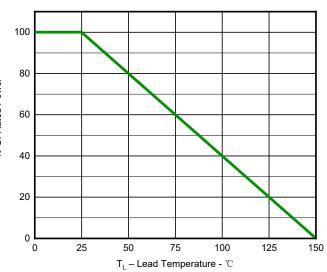
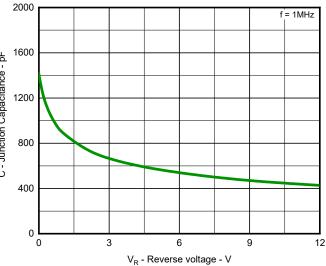
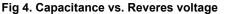
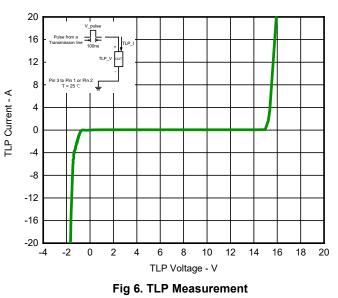


Fig 2.Power Derating Curve



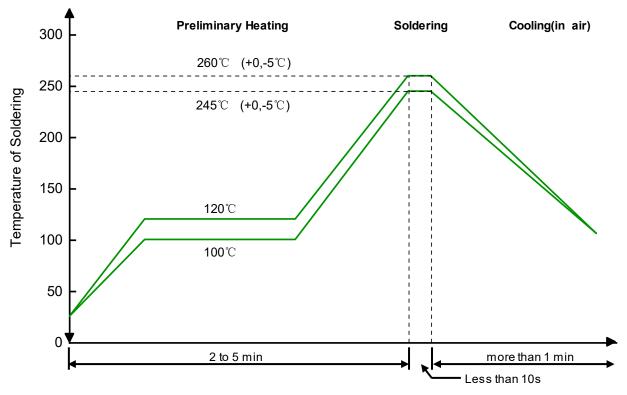




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Solder Reflow Recommendation



Remark: Pb free for 260°C; Pb for 245°C.

PCB Design

For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

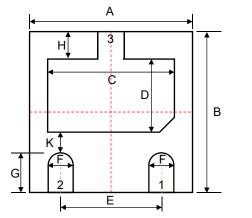
- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

Ordering information

Device	Package	Reel	Shipping
PTVSHC3N12VUT	DFN2020-3L (Pb-Free)	7"	3000 / Tape & Reel

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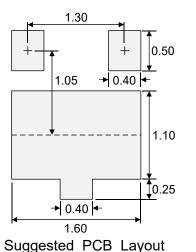
Product Dimension (DFN2020-3L)





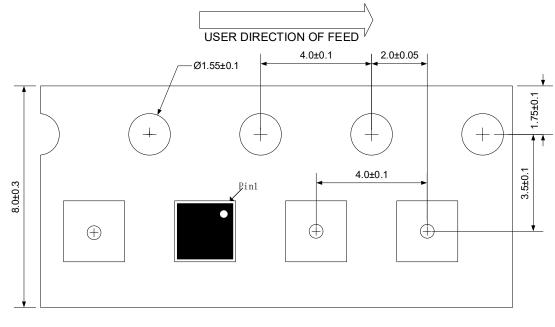
Bottom View

Side View



Unit:mm

Load with information



Unit:mm

PTVSHC3N12VUT

Inches

0.051 BSC

0.012 BSC

Max

0.083

0.083

0.063

0.045

0.014

0.018

0.012

0.024

Min

0.075

0.075

0.055

0.035

0.010

0.014

0.006

0.020

Millimeters

1.30 BSC

0.30 BSC

Max

2.10

2.10

1.60

1.15

0.35

0.45

0.30

0.60

Min

1.90

1.90

1.40

0.90

0.25

0.35

0.15

0.50

Dim

А

В

С

D

Е

F

G

н

J

Κ

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